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Contents

√ii	Authors	
ix	Conference Committee	
xi	Introduction	
	PLENARY SESSION	
10809 02	Accelerate lithography improvement for high performance computing (Plenary Paper) [10809-1]	
10809 03	Current challenges and opportunities for EUV lithography (Plenary Paper) [10809-2]	
	EUV SCANNER AND SOURCE	
10809 04	EUV industrialization high volume manufacturing with NXE3400B (Invited Paper) [10809-3]	
10809 05	NXE:3400B imaging performance assessed from a customer perspective [10809-4]	
10809 07	Accelerator-based compact extreme ultraviolet (EUV) sources for lithography [10809-6]	
	EUV PROCESS CONTROL	
	EGY I ROCESS GONINGE	
10809 09	EUV stochastic defect monitoring with advanced broadband optical wafer inspection and e-beam review systems (Invited Paper) [10809-8]	
10809 0A	Non-Gaussian CD distribution characterization for DRAM application in EUV lithography [10809-9]	
10809 OB	Measurement and modeling of diffusion characteristics in EUV resist [10809-10]	
10809 0C	Massive CD metrology for EUV failure characterization and EPE metrology [10809-11]	
	EUV MASK BLANKS: JOINT SESSION WITH CONFERENCES 10809 AND 10810	
10809 OF	lon beam processing for critical EUV photomask process steps: mask blank deposition and photomask absorber etch [10809-14]	

	EUV MASK AND IMAGING: JOINT SESSION WITH CONFERENCES 10809 AND 10810	
10809 0M	Optimization and stability of CD variability in pitch 40 nm contact holes on NXE:3300 [10809-20]	
10809 ON	EUV pupil optimization for 32nm pitch logic structures [10809-66]	
10809 00	Rapid image-based pupil plane characterization for EUV lithography systems [10809-22]	
	EUV PELLICLE AND METROLOGY: JOINT SESSION WITH CONFERENCES 10809 AND 10810	
10809 OR	Development of full-size EUV pellicle with thermal emission layer coating [10809-25]	
10809 OT	EUV mask characterization with actinic scatterometry [10809-27]	
	EUV MATERIALS II	
10809 OU	State-of-the-art of EUV materials for N5 logic and DRAM applications (Invited Paper) [10809-28]	
10809 0V	Using resonant soft x-ray scattering to image patterns on undeveloped resists [10809-29]	
10809 0X	New resist and underlayer approaches toward EUV lithography [10809-31]	
	PATTERNING	
10809 14	Integration via 3rd dimension: 3D power scaling (Invited Paper) [10809-38]	
10809 16	Study of resist hardmask interaction through surface activation layers [10809-40]	
	POSTER SESSION: EUV MASK	
10809 19	Optimization of absorber and multilayer in EUV mask for 1D and 2D patterns [10809-43]	
10809 1A	Holographic masks for computational proximity lithography with EUV radiation [10809-44]	
10809 1E	A tool for full area inband EUV transmission mapping of EUV pellicles [10809-49]	
10809 1G	Pattern degradation with larger particles on EUV pellicle [10809-51]	
10809 1H	Defect avoidance for extreme ultraviolet mask defects using intentional pattern deformation [10809-52]	

10809 11	AIMERTM: full reticle area, scanner-effective EUV mapping reflectometry [10809-53]
	POSTER SESSION: EUV SOURCE
10809 1L	NXE:3400B EUV source performance in the field, readiness for HVM and power scaling beyond 250W [10809-56]
10809 1M	Key components development progress of high-power LPP-EUV light source with unique debris mitigation system using a magnetic field [10809-57]
10809 1Q	Debris-free high-brightness light source based on LPP for actinic EUV microscopy and metrology applications [10809-61]
	POSTER SESSION: IMAGING/OPTICS
10809 1S	Lateral shearing interferometry for high-NA EUV wavefront metrology [10809-63]
10809 1T	Reflectance measurement of EUV mirrors with s- and p-polarized light using polarization controunits [10809-64]
10809 1U	Spatially resolved reflectometry for EUV optical components [10809-65]
	POSTER SESSION: MATERIALS
10809 1V	Actinic tools for EUV resist characterization in research and production [10809-67]
10809 1W	In-situ measurement of outgassing generated from EUV metal oxide nanoparticles resist during electron irradiation [10809-68]
10809 1X	EUV sensitizer for resists and spin-on-carbon materials [10809-69]
10809 1Y	Development of absorption-coefficient-measurement method of EUV resist by direct-resist coating on a photodiode [10809-70]
	POSTER SESSION: PROCESS CONTROL
10809 24	Improvement of CD stability and defectivity in resist coating and developing process in EUV lithography process [10809-76]